PD - 93936A

International
IOR Rectifier

SMPS MOSFET

IRF3706
IRF3706S
IRF3706L

HEXFET® Power MOSFET

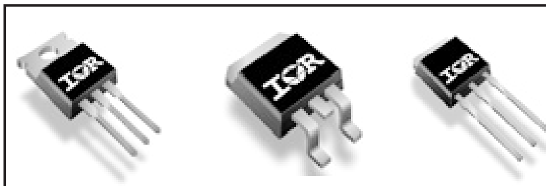
Applications

- High Frequency Isolated DC-DC Converters with Synchronous Rectification for Telecom and Industrial Use
- High Frequency Buck Converters for Computer Processor Power

Benefits

- Ultra-Low Gate Impedance
- Very Low $R_{DS(on)}$ at 4.5V V_{GS}
- Fully Characterized Avalanche Voltage and Current

V_{DSS}	$R_{DS(on)}$ max	I_D
20V	**8.5mΩ**	**77A**



TO-220AB IRF3706 | D²Pak IRF3706S | TO-262 IRF3706L

Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-to-Source Voltage	± 12	V
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V	77	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V	54	
I_{DM}	Pulsed Drain Current①	280	
P_D @T_C = 25°C	Maximum Power Dissipation③	88	W
P_D @T_C = 100°C	Maximum Power Dissipation③	44	W
	Linear Derating Factor	0.59	W/°C
T_J , T_{STG}	Junction and Storage Temperature Range	-55 to + 175	°C

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	——	1.7	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface ④	0.50	——	
$R_{\theta JA}$	Junction-to-Ambient④	——	62	
$R_{\theta JA}$	Junction-to-Ambient (PCB mount)⑤	——	40	

Notes ① through ⑤ are on page 11

Static @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	20	–––	–––	V	V_{GS} = 0V, I_D = 250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	–––	0.021	–––	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	–––	6.0	8.5	mΩ	V_{GS} = 10V, I_D = 36A ③
		–––	7.3	10.5		V_{GS} = 4.5V, I_D = 28A ③
		–––	11	22		V_{GS} = 2.8V, I_D = 18A ③
$V_{GS(th)}$	Gate Threshold Voltage	0.6	–––	2.0	V	V_{DS} = V_{GS}, I_D = 250µA
I_{DSS}	Drain-to-Source Leakage Current	–––	–––	20	µA	V_{DS} = 16V, V_{GS} = 0V
		–––	–––	100		V_{DS} = 16V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Forward Leakage	–––	–––	200	nA	V_{GS} = 12V
	Gate-to-Source Reverse Leakage	–––	–––	-200		V_{GS} = -12V

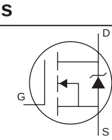
Dynamic @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	53	–––	–––	S	V_{DS} = 16V, I_D = 57A
Q_g	Total Gate Charge	–––	23	35	nC	I_D = 28A
Q_{gs}	Gate-to-Source Charge	–––	8.0	12		V_{DS} = 10V
Q_{gd}	Gate-to-Drain ("Miller") Charge	–––	5.5	8.3		V_{GS} = 4.5V ③
Q_{oss}	Output Gate Charge	–––	16	24		V_{GS} = 0V, V_{DS} = 10V
$t_{d(on)}$	Turn-On Delay Time	–––	6.8	–––	ns	V_{DD} = 10V
t_r	Rise Time	–––	87	–––		I_D = 28A
$t_{d(off)}$	Turn-Off Delay Time	–––	17	–––		R_G = 1.8Ω
t_f	Fall Time	–––	4.8	–––		V_{GS} = 4.5V ③
C_{iss}	Input Capacitance	–––	2410	–––	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	–––	1070	–––		V_{DS} = 10V
C_{rss}	Reverse Transfer Capacitance	–––	140	–––		ƒ = 1.0MHz

Avalanche Characteristics

Symbol	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy②	–––	220	mJ
I_{AR}	Avalanche Current①	–––	28	A

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	–––	–––	77	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	–––	–––	280		
V_{SD}	Diode Forward Voltage	–––	0.88	1.3	V	T_J = 25°C, I_S = 36A, V_{GS} = 0V ③
		–––	0.82	–––		T_J = 125°C, I_S = 36A, V_{GS} = 0V ③
t_{rr}	Reverse Recovery Time	–––	45	68	ns	T_J = 25°C, I_F = 36A, V_R=20V
Q_{rr}	Reverse Recovery Charge	–––	65	98	nC	di/dt = 100A/µs ③
t_{rr}	Reverse Recovery Time	–––	49	74	ns	T_J = 125°C, I_F = 36A, V_R=20V
Q_{rr}	Reverse Recovery Charge	–––	78	120	nC	di/dt = 100A/µs ③

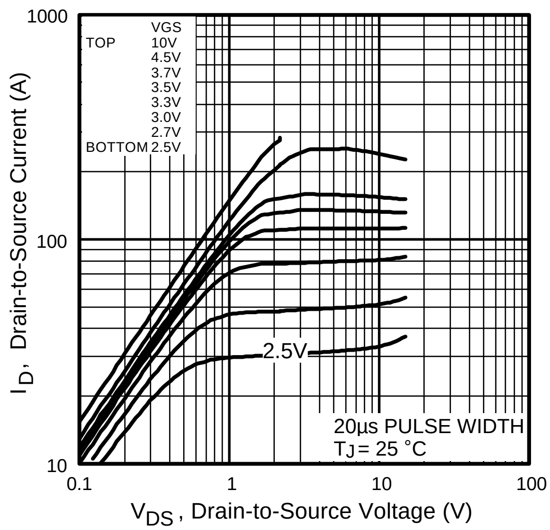


Fig 1. Typical Output Characteristics

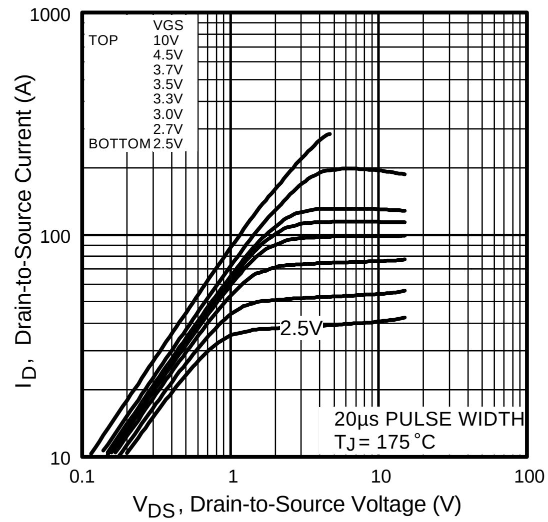


Fig 2. Typical Output Characteristics

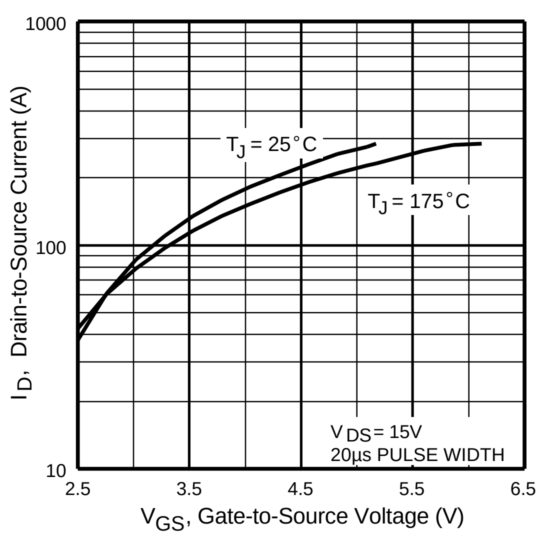


Fig 3. Typical Transfer Characteristics

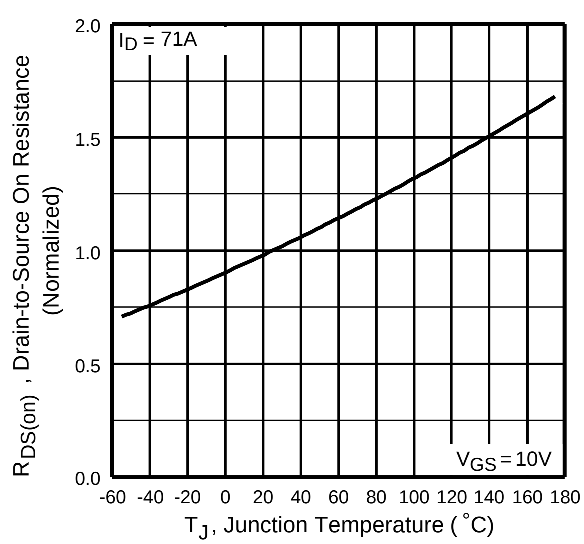


Fig 4. Normalized On-Resistance Vs. Temperature

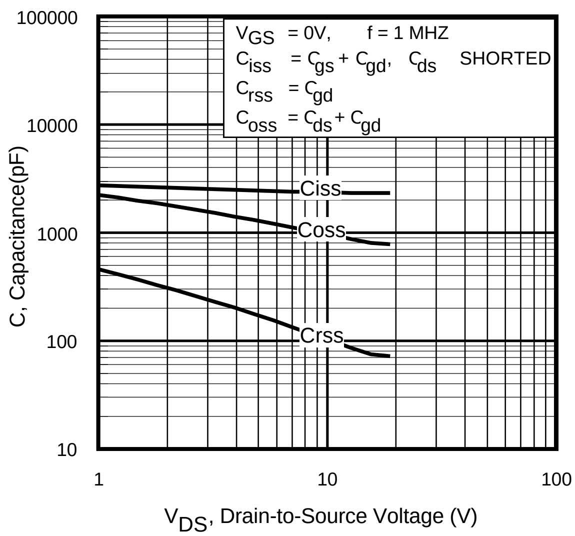


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

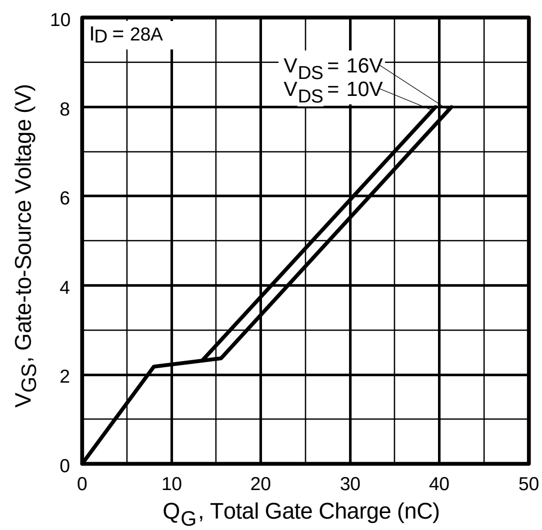


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

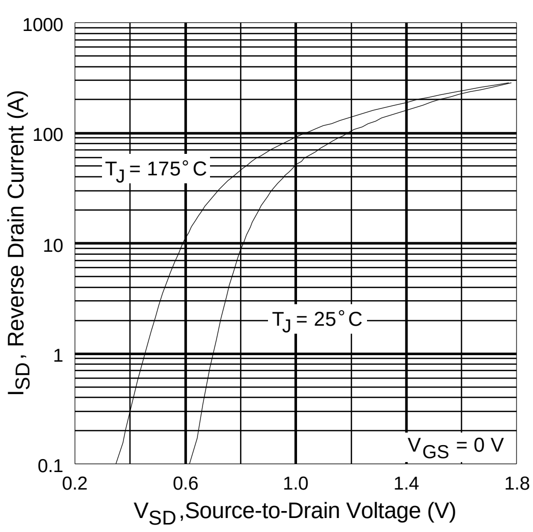


Fig 7. Typical Source-Drain Diode Forward Voltage

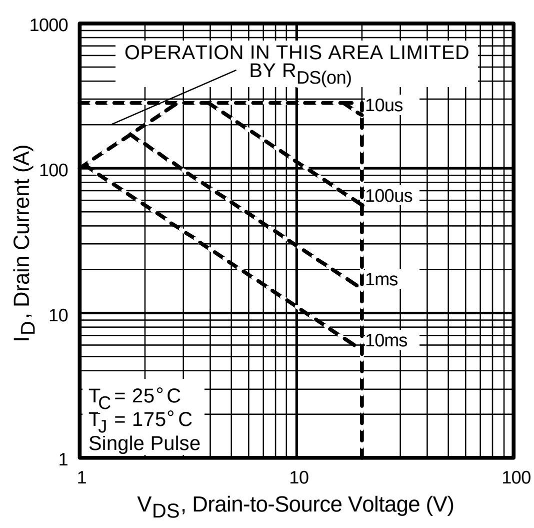


Fig 8. Maximum Safe Operating Area

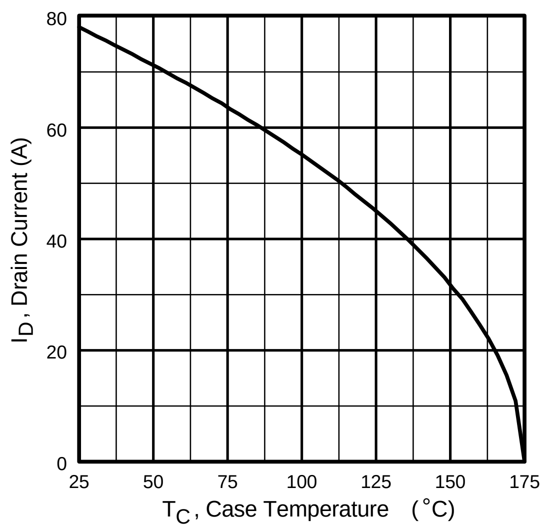


Fig 9. Maximum Drain Current Vs. Case Temperature

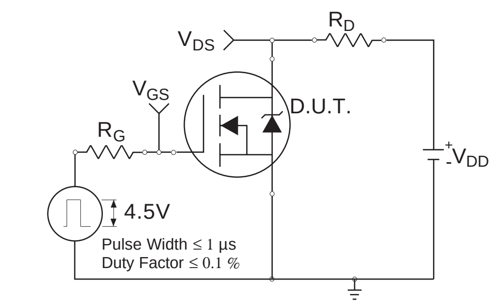


Fig 10a. Switching Time Test Circuit

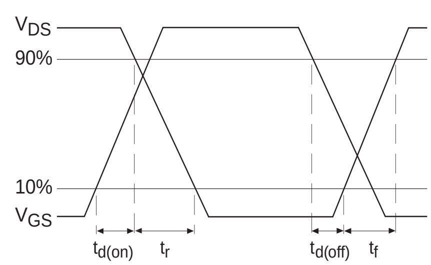


Fig 10b. Switching Time Waveforms

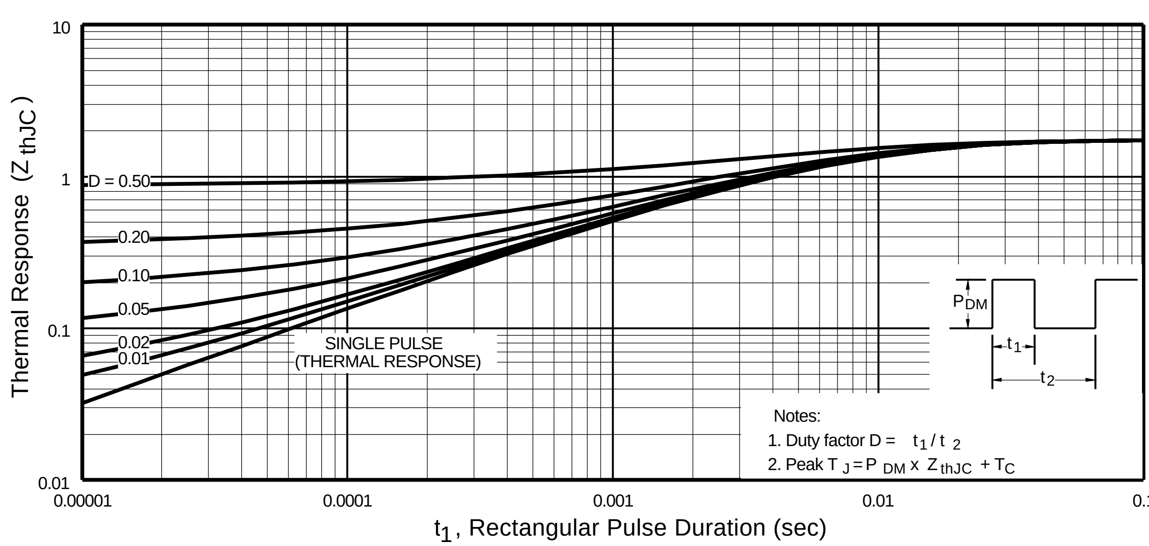


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

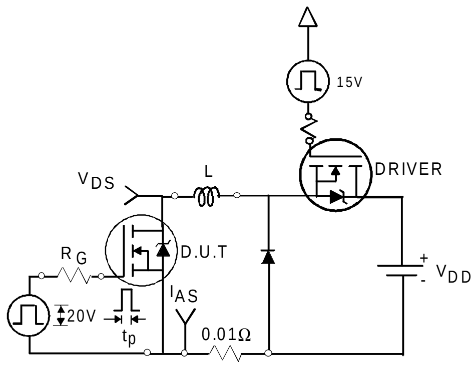


Fig 12a. Unclamped Inductive Test Circuit

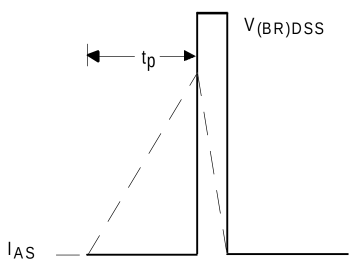


Fig 12b. Unclamped Inductive Waveforms

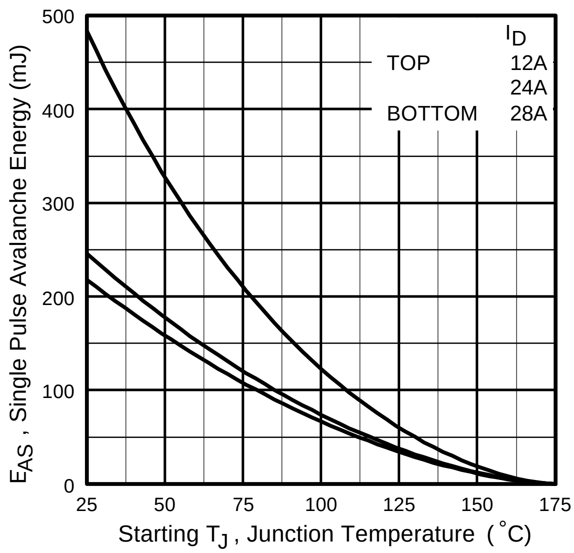


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

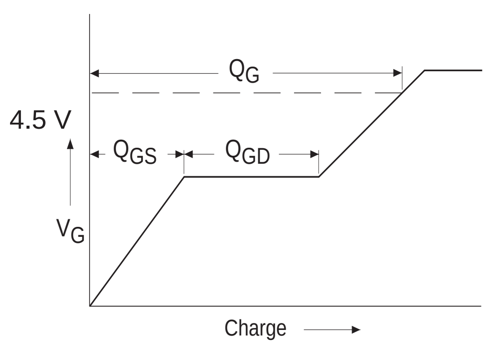


Fig 13a. Basic Gate Charge Waveform

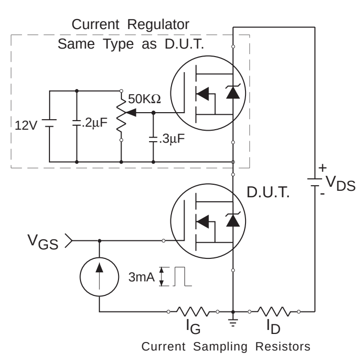
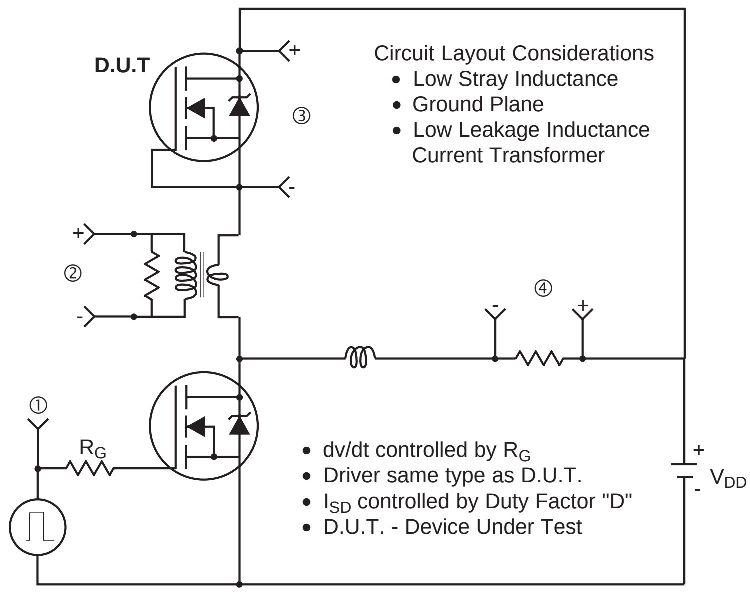
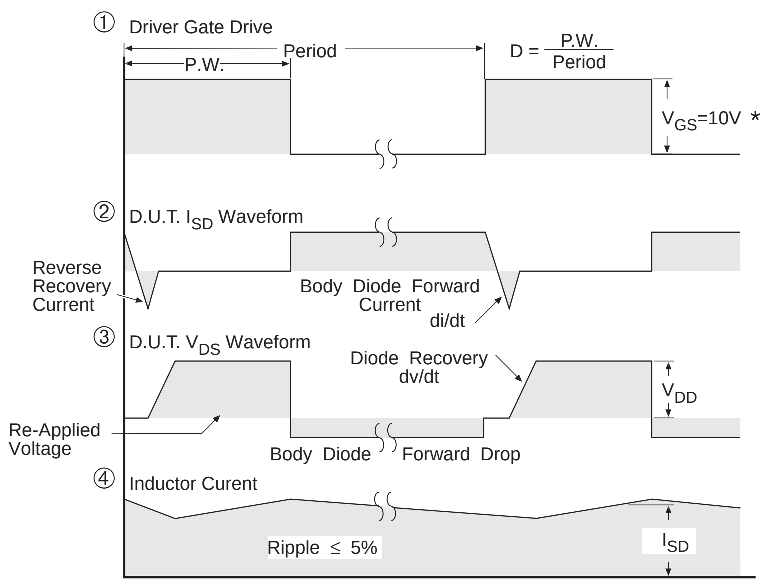


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



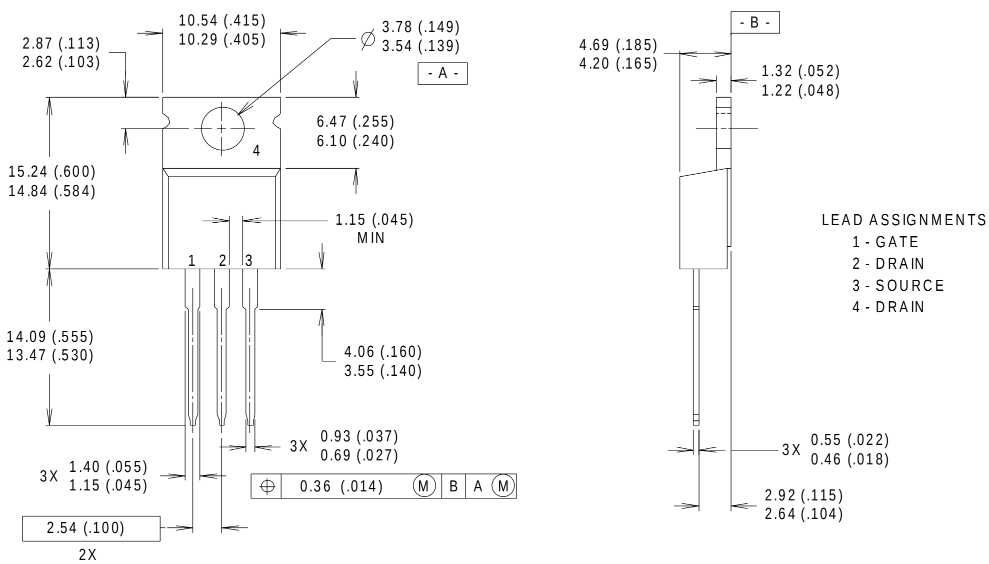


* V_{GS} = 5V for Logic Level Devices

Fig 14. For N-Channel HEXFET® Power MOSFETs

TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.

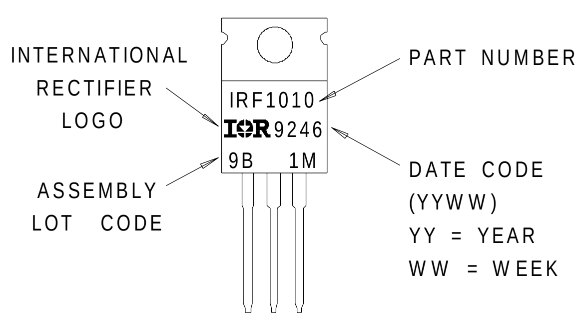
2 CONTROLLING DIMENSION : INCH

3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.

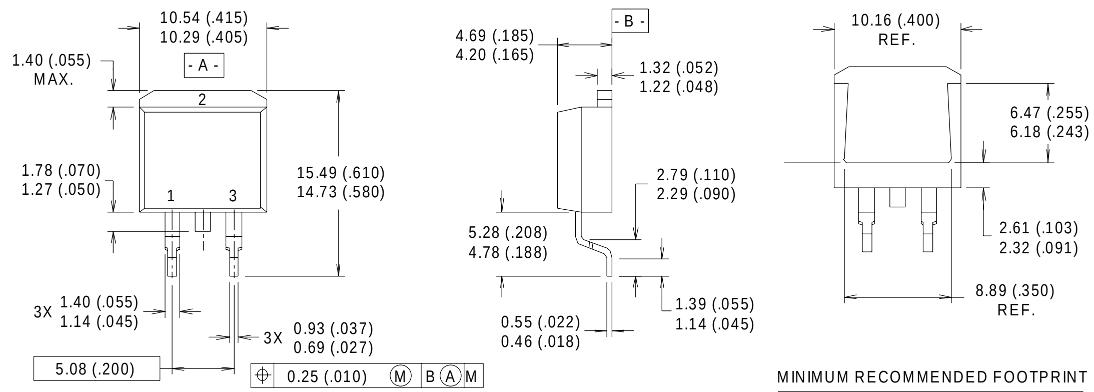
4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

TO-220AB Part Marking Information

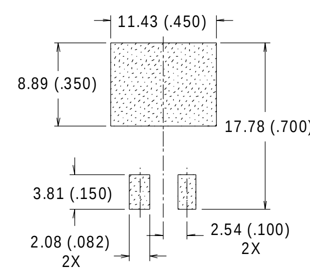
EXAMPLE : THIS IS AN IRF1010
WITH ASSEMBLY
LOT CODE 9B1M



D²Pak Package Outline



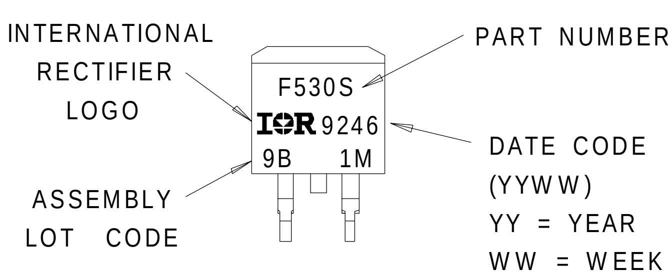
MINIMUM RECOMMENDED FOOTPRINT



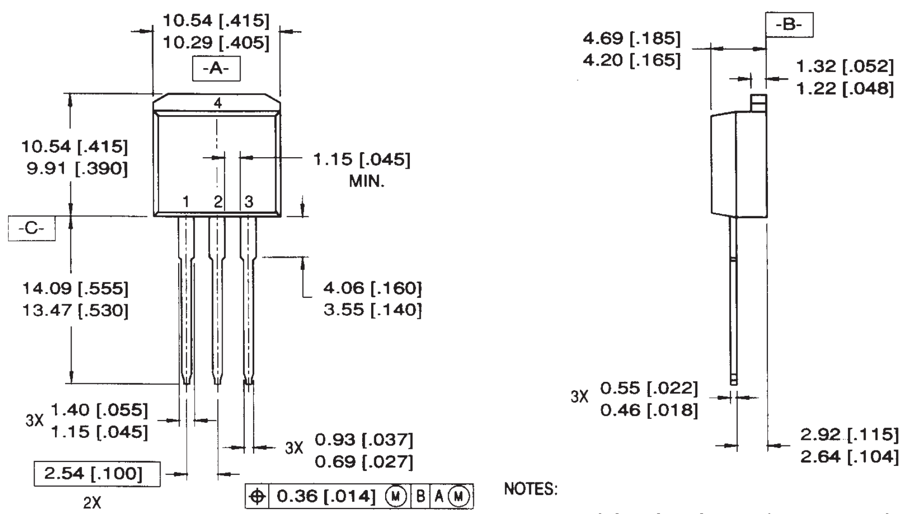
NOTES:
1. DIMENSIONS AFTER SOLDER DIP.
2. DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
3. CONTROLLING DIMENSION : INCH.
4. HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

LEAD ASSIGNMENTS
1 - GATE
2 - DRAIN
3 - SOURCE

D²Pak Part Marking Information



TO-262 Package Outline



LEAD ASSIGNMENTS

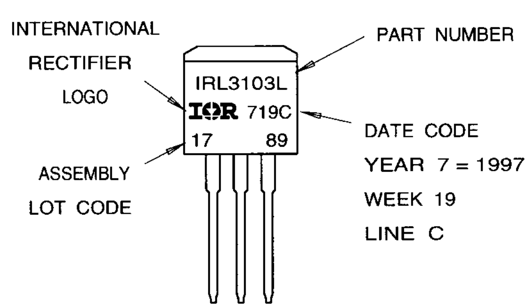
1 = GATE
2 = DRAIN
3 = SOURCE
4 = DRAIN

NOTES:

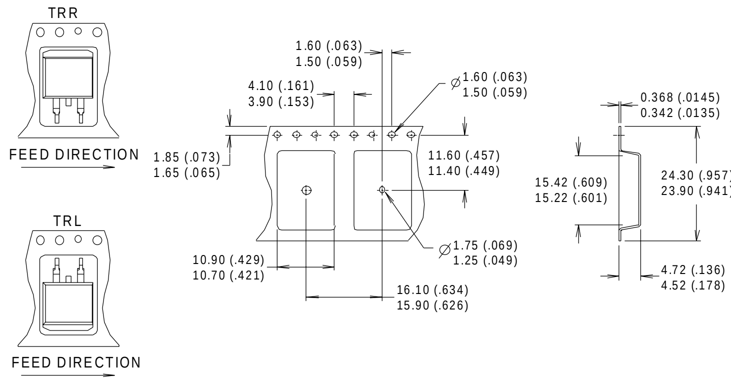
1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

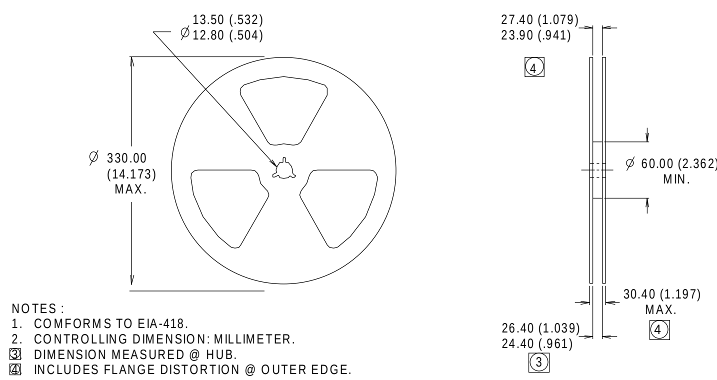
TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"



D^2Pak Tape & Reel Information





Notes:

① Repetitive rating; pulse width limited by max. junction temperature.

② Starting T_J = 25°C, L = 0.54mH R_G = 25Ω, I_{AS} = 28A.

③ Pulse width ≤ 400µs; duty cycle ≤ 2%.

④ This is only applied to TO-220AB package

⑤ This is applied to D^2Pak, when mounted on 1" square PCB (FR-4 or G-10 Material).
For recommended footprint and soldering techniques refer to application note #AN-994.

International
IOR Rectifier

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IR CANADA: 15 Lincoln Court, Brampton, Ontario L6T3Z2, Tel: (905) 453 2200
IR GERMANY: Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 (0) 6172 96590
IR ITALY: Via Liguria 49, 10071 Borgaro, Torino Tel: ++ 39 011 451 0111
IR JAPAN: K&H Bldg., 2F, 30-4 Nishi-Ikebukuro 3-Chome, Toshima-Ku, Tokyo 171 Tel: 81 (0)3 3983 0086
IR SOUTHEAST ASIA: 1 Kim Seng Promenade, Great World City West Tower, 13-11, Singapore 237994 Tel: ++ 65 (0)838 4630
IR TAIWAN:16 Fl. Suite D. 207, Sec. 2, Tun Haw South Road, Taipei, 10673 Tel: 886-(0)2 2377 9936